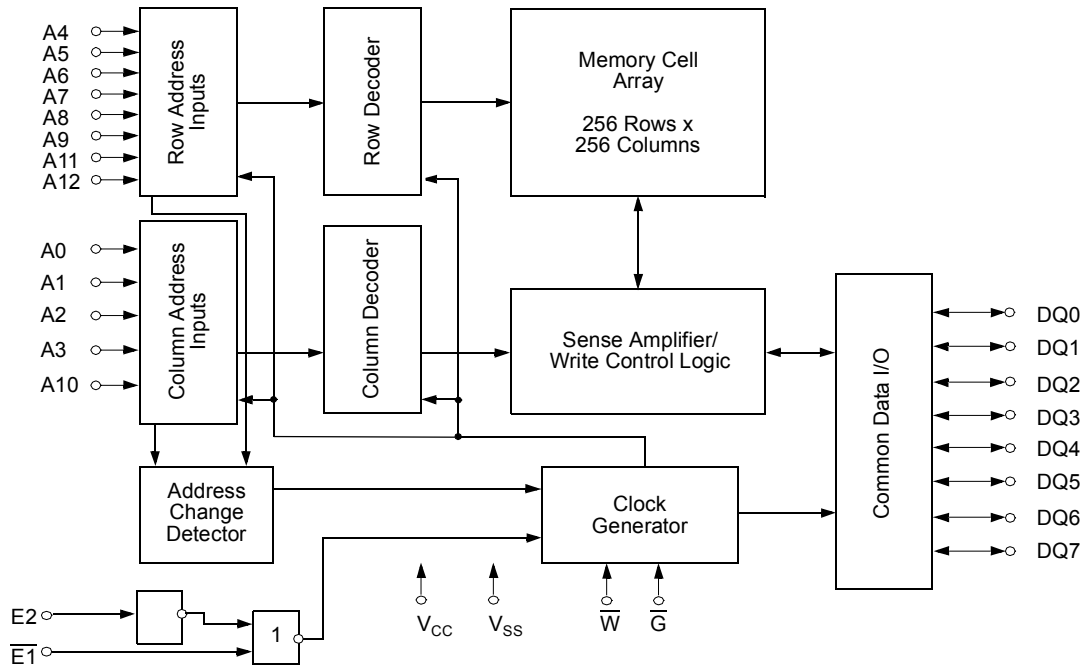


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Block Diagram



Truth Table

Operating Mode	$\overline{E1}$	E2	\overline{W}	\overline{G}	DQ0 - DQ7
Standby/not selected	*	L	*	*	High-Z
	H	*	*	*	High-Z
Internal Read	L	H	H	H	High-Z
Read	L	H	H	L	Data Outputs Low-Z
Write	L	H	L	*	Data Inputs High-Z

* H or L

Characteristics

All voltages are referenced to $V_{SS} = 0$ V (ground).

All characteristics are valid in the power supply voltage range and in the operating temperature range specified.

Dynamic measurements are based on a rise and fall time of ≤ 5 ns, measured between 10 % and 90 % of V_I , as well as input levels of $V_{IL} = 0$ V and $V_{IH} = 3$ V. The timing reference level of all input and output signals is 1.5 V, with the exception of the t_{dis} -times, in which cases transition is measured ± 200 mV from steady-state voltage.

Absolute Maximum Ratings ^a		Symbol	Min.	Max.	Unit
Power Supply Voltage		V_{CC}	-0.3	7	V
Input Voltage		V_I	-0.3	$V_{CC} + 0.5$ ^b	V
Output Voltage		V_O	-0.3	$V_{CC} + 0.5$ ^b	V
Power Dissipation		P_D	-	1	W
Operating Temperature	C-Type	T_a	0	70	°C
	K-Type		-40	85	°C
	A-Type		-40	125	°C
Storage Temperature	C/K-Type	T_{stg}	-55	125	°C
	A-Type		-65	150	°C
Output Short-Circuit Current at $V_{CC} = 5$ V and $V_O = 0$ V ^c		$ I_{OS} $		100	mA

^a Stresses greater than those listed under „Absolute Maximum Ratings“ may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at condition above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability

^b Maximum voltage is 7 V

^c Not more than 1 output should be shorted at the same time. Duration of the short circuit should not exceed 30 s.

Recommended Operating Conditions	Symbol	Conditions	Min.	Max.	Unit
Power Supply Voltage	V_{CC}		4.5	5.5	V
Data Retention Voltage	$V_{CC(DR)}$		2.0		V
Input Low Voltage ^d	V_{IL}		-0.3	0.8	V
Input High Voltage	V_{IH}		2.2	$V_{CC} + 0.3$	V

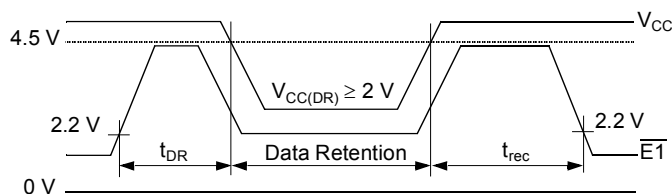
^d -2 V at Pulse Width 10 ns

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Electrical Characteristics	Symbol	Conditions	Min.	Max.	Unit
Supply Current - Operating Mode	$I_{CC(OP)}$	$V_{CC} = 5.5\text{ V}$ $V_{IL} = 0.8\text{ V}$ $V_{IH} = 2.2\text{ V}$ $t_{cW} = 70\text{ ns}$		55	mA
Supply Current - Standby Mode (CMOS level)	$I_{CC(SB)}$	$V_{CC} = 5.5\text{ V}$ $V_{E1} = V_{E2} = V_{CC} - 0.2\text{ V}$ or $V_{E2} = 0.2\text{ V}$ C-Type K-Type A-Type		2 5 100	μA μA μA
Supply Current - Standby Mode (TTL level)	$I_{CC(SB)1}$	$V_{CC} = 5.5\text{ V}$ $V_{E1} = V_{E2} = 2.2\text{ V}$ or $V_{E2} = 0.8\text{ V}$		3	mA
Supply Current - Data Retention Mode	$I_{CC(DR)}$	$V_{CC(DR)} = 2\text{ V}$ $V_{E1} = V_{E2} = V_{CC(DR)} - 0.2\text{ V}$ or $V_{E2} = 0.2\text{ V}$ C-Type K-Type A-Type		1 3 50	μA μA μA
Output High Voltage	V_{OH}	$V_{CC} = 4.5\text{ V}$ $I_{OH} = -1.0\text{ mA}$	2.4		V
Output Low Voltage	V_{OL}	$V_{CC} = 4.5\text{ V}$ $I_{OL} = 3.2\text{ mA}$		0.4	V
Output High Current	I_{OH}	$V_{CC} = 4.5\text{ V}$ $V_{OH} = 2.4\text{ V}$		-1	mA
Output Low Current	I_{OL}	$V_{CC} = 4.5\text{ V}$ $V_{OL} = 0.4\text{ V}$	3.2		mA
Input Leakage Current High	I_{IH}	$V_{CC} = 5.5\text{ V}$ $V_{IH} = 5.5\text{ V}$ C/K-Type A-Type	- -	1 2	μA μA
Low	I_{IL}	$V_{CC} = 5.5\text{ V}$ $V_{IL} = 0\text{ V}$ C/K-Type A-Type	-1 -2	- -	μA μA
Output Leakage Current High at Three-State Outputs	I_{OHZ}	$V_{CC} = 5.5\text{ V}$ $V_{OH} = 5.5\text{ V}$ C/K-Type A-Type	- -	1 2	μA μA
Low at Three-State Outputs	I_{OLZ}	$V_{CC} = 5.5\text{ V}$ $V_{OL} = 0\text{ V}$ C/K-Type A-Type	-1 -2	- -	μA μA

Switching Characteristics	Symbol		Min.	Max.	Unit
	Alt.	IEC			
Time to Output in Low-Z	t_{LZ}	$t_{t(QX)}$	5	10	ns
Cycle Time					
Write Cycle Time	t_{WC}	t_{cW}	70		ns
Read Cycle Time	t_{RC}	t_{cR}	70		ns
Access Time					
$\overline{E1}$ LOW or E2 HIGH to Data Valid	t_{ACE}	$t_{a(E)}$	-	70	ns
\overline{G} LOW to Data Valid	t_{OE}	$t_{a(G)}$	-	40	ns
Address to Data Valid	t_{AA}	$t_{a(A)}$	-	70	ns
Pulse Widths					
Write Pulse Width	t_{WP}	$t_{w(W)}$	50		ns
Chip Enable to End of Write	t_{CW}	$t_{w(E)}$	65		ns
Setup Times					
Address Setup Time	t_{AS}	$t_{su(A)}$	0		ns
Chip Enable to End of Write	t_{CW}	$t_{su(E)}$	65		ns
Write Pulse Width	t_{WP}	$t_{su(W)}$	50		ns
Data Setup Time	t_{DS}	$t_{su(D)}$	35		ns
Data Hold Time	t_{DH}	$t_{h(D)}$	0		ns
Address Hold from End of Write	t_{AH}	$t_{h(A)}$	0		ns
Output Hold Time from Address Change	t_{OH}	$t_{v(A)}$	5		ns
$\overline{E1}$ HIGH or E2 LOW to Output in High-Z	t_{HZCE}	$t_{dis(E)}$	0	25	ns
\overline{W} LOW to Output in High-Z	t_{HZWE}	$t_{dis(W)}$	0	30	ns
\overline{G} HIGH to Output in High-Z	t_{HZOE}	$t_{dis(G)}$	0	25	ns

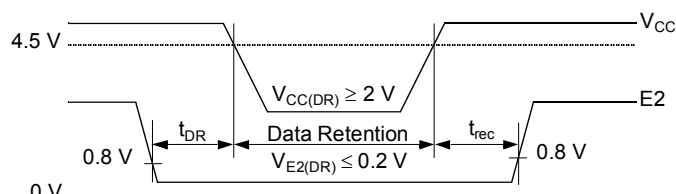
Data Retention Mode $\overline{E1}$ -Controlled



$$V_{E2(DR)} \geq V_{CC(DR)} - 0.2 \text{ V or } V_{E2(DR)} \leq 0.2 \text{ V}$$

$$V_{CC(DR)} - 0.2 \text{ V} \leq V_{E1(DR)} \leq V_{CC(DR)} + 0.3 \text{ V}$$

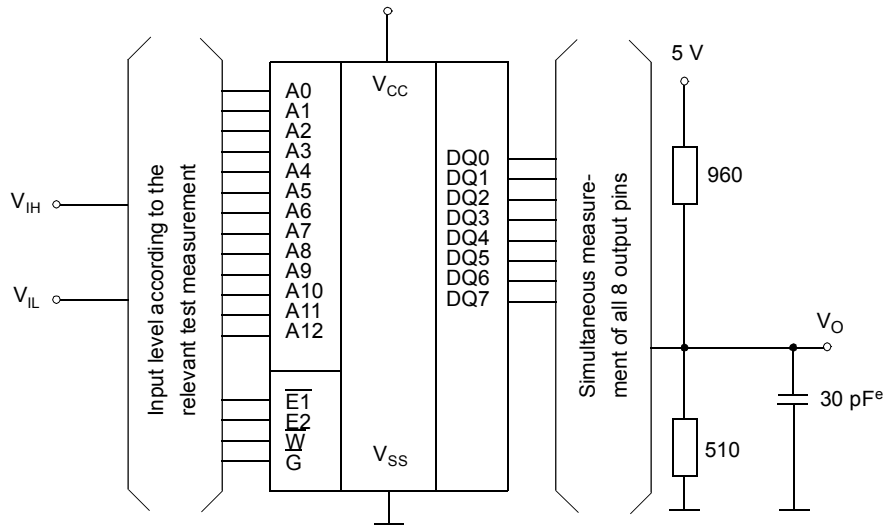
Data Retention Mode E2-Controlled



Chip Deselect to Data Retention Time t_{DR} : min 0 ns
 Operating Recovery Time t_{rec} : min t_{cR}

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Test Configuration for Functional Check

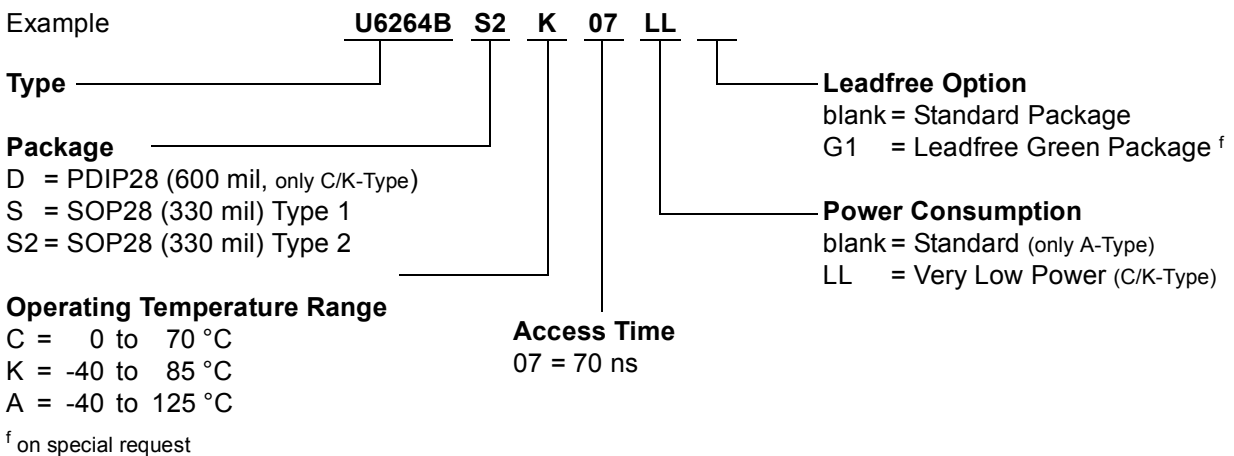


^e In measurement of $t_{dis(E)}$, $t_{dis(W)}$, $t_{dis(G)}$ the capacitance is 5 pF.

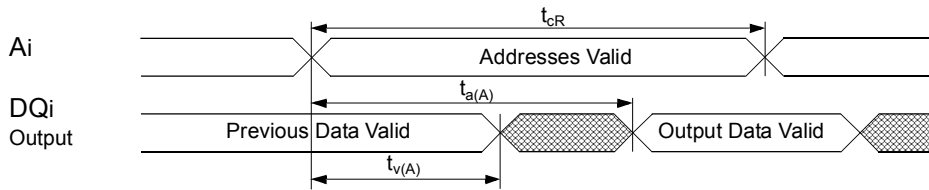
Capacitance	Conditions	Symbol	Min.	Max.	Unit
Input Capacitance	$V_{CC} = 5.0\text{ V}$ $V_I = V_{SS}$	C_I		8	pF
Output Capacitance	$f = 1\text{ MHz}$ $T_a = 25\text{ }^\circ\text{C}$	C_O		10	pF

All pins not under test must be connected with ground by capacitors.

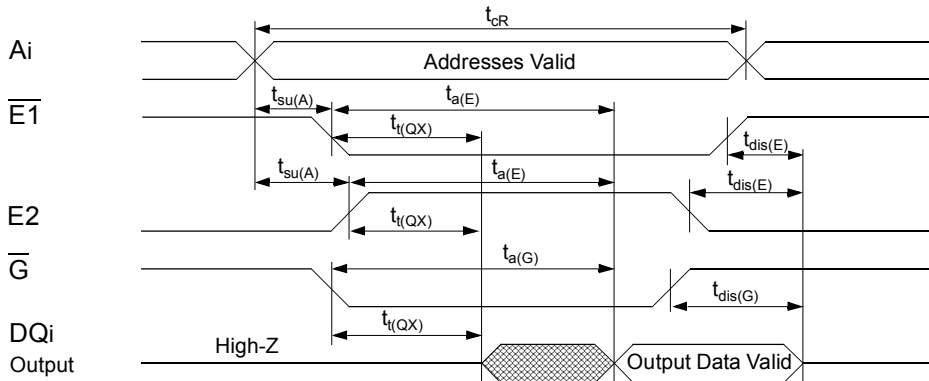
Ordering Code



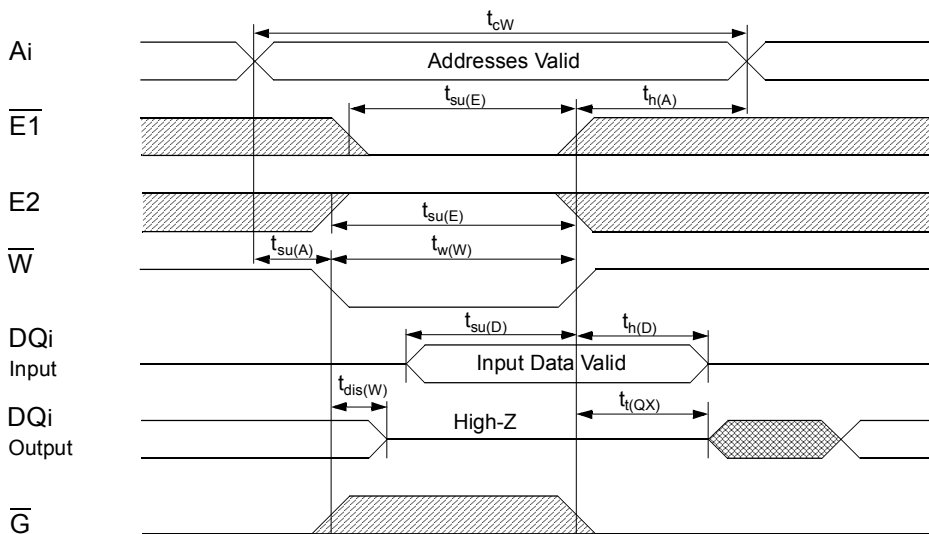
Read Cycle 1 (during Read cycle: $\overline{E1} = \overline{G} = V_{IL}$, $E2 = \overline{W} = V_{IH}$)



Read Cycle 2 (during Read cycle: $\overline{W} = V_{IH}$)

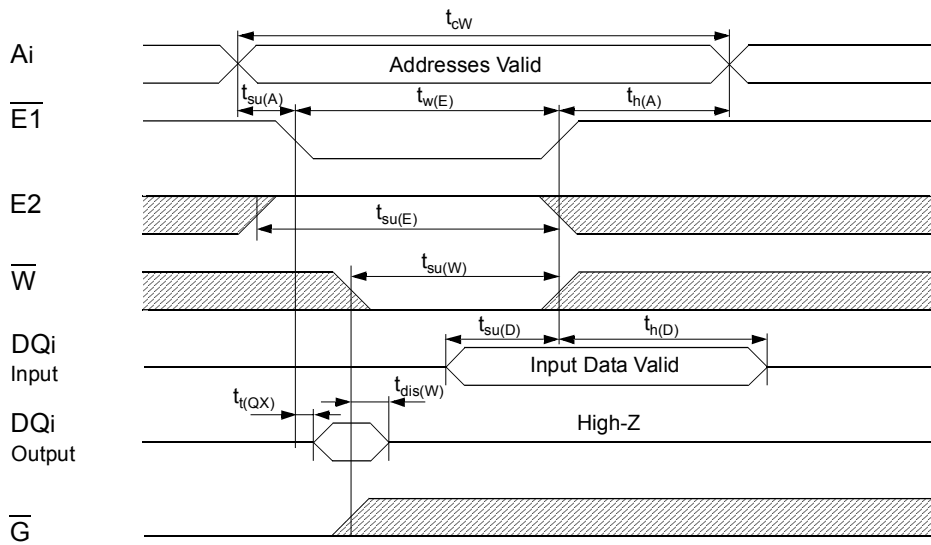


Write Cycle 1 (\overline{W} -controlled)

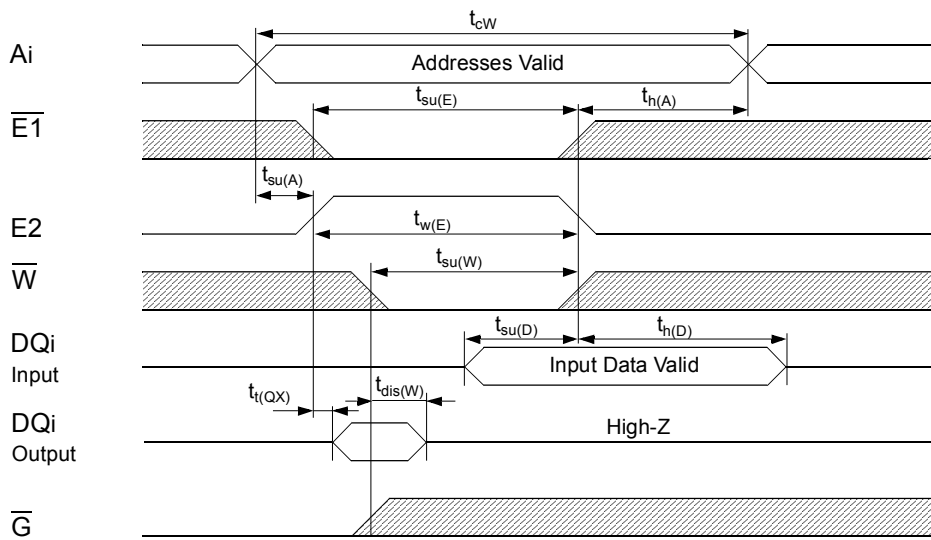


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Write Cycle 2 ($\overline{E1}$ -controlled)



Write Cycle 3 (E2-controlled)



undefined



L- or H-level



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